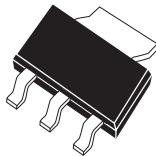


CZTA44

**NPN SILICON EXTREMELY
HIGH VOLTAGE TRANSISTOR**



SOT-223 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZTA44 type is a surface mount epoxy molded silicon planar epitaxial transistors designed for extremely high voltage applications.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

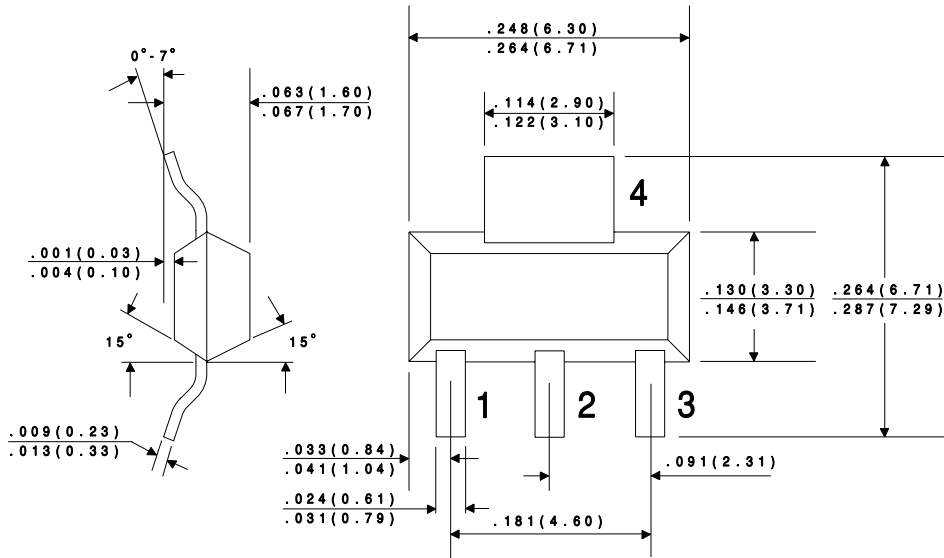
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	450	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	300	mA
Power Dissipation	P_D	2.0	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	Θ_{JA}	62.5	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=400\text{V}$		100	nA
I_{CES}	$V_{CE}=400\text{V}$		500	nA
I_{EBO}	$V_{BE}=4.0\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	450		V
BV_{CES}	$I_C=100\mu\text{A}$	450		V
BV_{CEO}	$I_C=1.0\text{mA}$	400		V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=1.0\text{mA}, I_B=0.1\text{mA}$		0.40	V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.50	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.75	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.75	V
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	40		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	50	200	
h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$	45		

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=10V, I_C=100mA$	20		
f_T	$V_{CE}=10V, I_C=10mA, f=10MHz$	20		MHz
C_{ob}	$V_{CB}=20V, I_E=0, f=1.0MHz$		7.0	pF
C_{ib}	$V_{EB}=0.5V, I_C=0, f=1.0MHz$		130	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR